AUK Semiconductor

SRC1202E

NPN Silicon Transistor

Descriptions

- Switching application
- Interface circuit and driver circuit application

Features

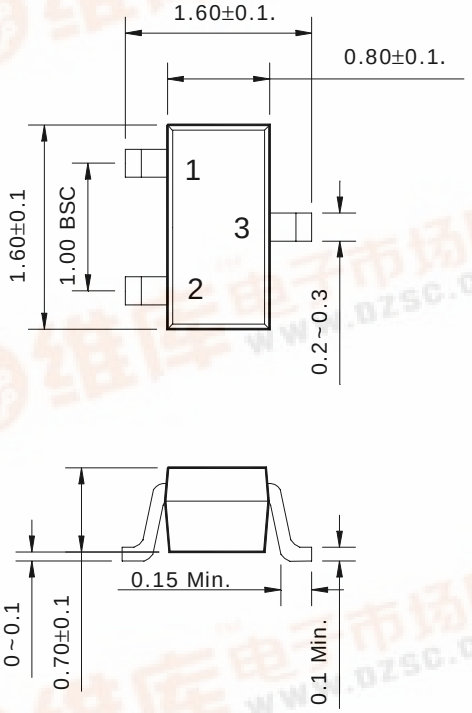
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- High packing density

Ordering Information

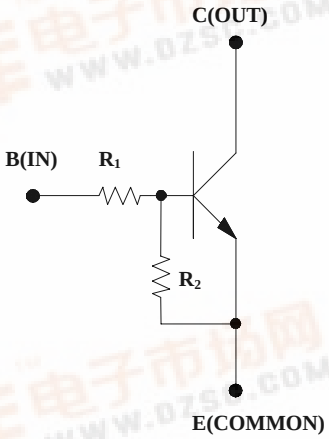
Type NO.	Marking	Package Code
SRC1202E	R2	SOT-523

Outline Dimensions

unit : mm



• Equivalent Circuit



PIN Connections

1. Base
2. Emitter
3. Collector

R_1	R_2
10KΩ	10KΩ

Absolute maximum ratings (Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Out Voltage	V_O	50	V
Input Voltage	V_I	30	V
Out Current	I_O	100	mA
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 ~ 150	°C

Electrical Characteristics (Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Output Cut-off Current	$I_{O(OFF)}$	V_O=50V, V_I=0	-	-	500	nA
DC Current Gain	G_I	V_O=5V, I_O=10mA	50	80	-	-
Output Voltage	$V_{O(ON)}$	I_O=10mA, I_I=0.5mA	-	0.1	0.3	V
Input Voltage (ON)	$V_{I(ON)}$	V_O=0.2V, I_O=5mA	-	1.8	2.4	V
Input Voltage (OFF)	$V_{I(OFF)}$	V_O=5V, I_O=0.1mA	1.0	1.2	-	V
Transition Frequency	f_T*	V_O=10V, I_O=5mA	-	200	-	MHz
Input Current	I_I	V_I=5V	-	-	0.88	mA

* : Characteristic of Transistor Only

Electrical Characteristic Curves

Fig. 1 I_O - $V_{I(ON)}$

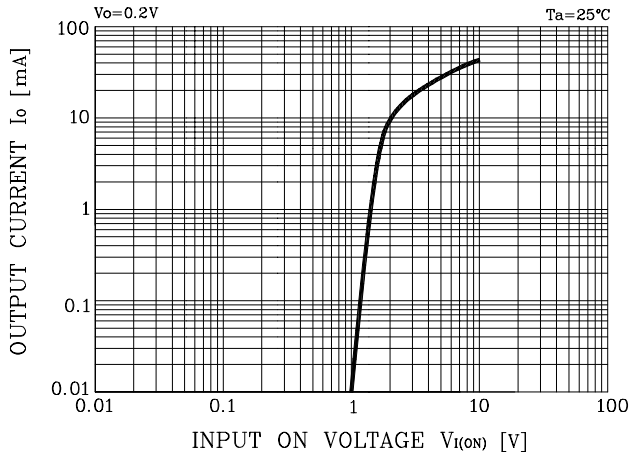


Fig. 2 I_O - $V_{I(OFF)}$

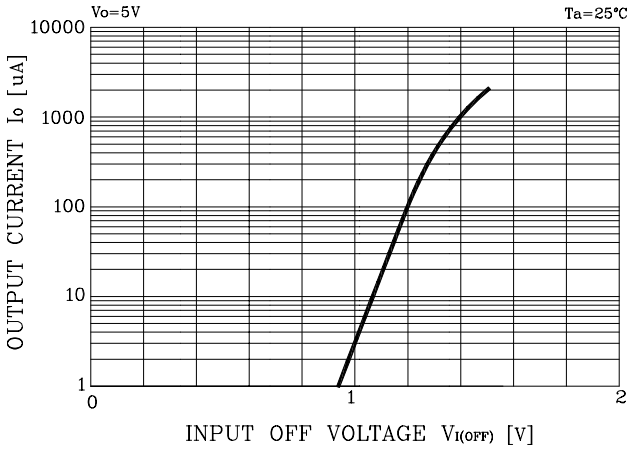


Fig. 3 G_I - I_O